



Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) An electro-optical device comprising, above a substrate:
  - a data line extending in a first direction;
  - a scanning line extending in a second direction and intersecting the data line;
  - a pixel electrode and a thin film transistor disposed so as to correspond to an intersection region of the data line and the scanning line;
  - a storage capacitor electrically connected to the thin film transistor and the pixel electrode, the storage capacitor including a pixel-potential-side capacitor electrode and a fixed-potential-side capacitor electrode; and
  - a light-blocking shield layer disposed above the thin film transistor at a position between the data line and the pixel electrode, the light-blocking shield layer covering the data line, the light-blocking shield layer and including a lower layer formed from aluminum and an upper layer formed from titanium nitride; the light-blocking shield layer having a fixed potential and being electrically connected to the fixed-potential-side capacitor electrode of the capacitor, the light-blocking shield layer having two edges running substantially in parallel with each other, one edge including an indented portion that recedes inward from the rest of the one edge;
  - a first relay layer formed in a same layer above the substrate as the light-blocking shield layer and electrically connected to the pixel electrode;
  - an insulating interlayer disposed below the first relay layer;
  - a second relay layer formed in a different layer above the substrate than the light-blocking shield layer and the first relay layer with the second relay layer disposed on one side of the insulating interlayer, and the light-blocking shield layer and the first relay layer

disposed on the other side of the insulating interlayer, the second relay layer being electrically connected to the pixel-potential-side capacitor electrode of the capacitor; and

a contact hole electrically connecting the first relay layer to the second relay layer through a portion of the insulating interlayer that corresponds to the indented portion of the light-blocking shield layer so that the pixel electrode is electrically connected to the pixel-potential-side capacitor electrode of the capacitor,

wherein the second relay layer covers the indented portion of the light-blocking shield layer in plan view to provide a light shield at the indented portion,

the thin film transistor includes a semiconductor layer having a channel region that extends in a longitudinal direction and a channel adjacent region that further extends from the channel region in the longitudinal direction, and

the scanning line includes a light-shielding part disposed at a side of the channel region.

2. (Canceled)

3. (Previously Presented) The electro-optical device according to Claim 1, the scanning line including a main-body part extending in a direction that intersects the longitudinal direction and a gate electrode of the thin film transistor overlapped with the channel region in plan view, and a horizontal protrusion protruding from the main-body part at the side of the channel region in the longitudinal direction in plan view and constituting a light-shielding part.

4. (Previously Presented) The electro-optical device according to Claim 3, the main-body part and the horizontal protrusion being integrally formed of the same film.

5. (Previously Presented) The electro-optical device according to Claim 3, the horizontal protrusion protruding from source and drain sides of the channel region in plan view.

6. (Previously Presented) The electro-optical device according to Claim 1, the thin film transistor including a semiconductor layer having a channel region that extends in a longitudinal direction,

the electro-optical device, further comprising:

an upper light-shielding film at least covering the channel region of the thin film transistor from the upper side, and

at least a part of the upper light-shielding film being formed in a concave shape in a cross section perpendicular to the longitudinal direction of the channel region as viewed from the channel region.

7. (Withdrawn) The electro-optical device according to Claim 1, the thin film transistor including a semiconductor layer having a channel region that extends in the first direction, and

the scanning line including a main-line part including a gate electrode of the thin film transistor that faces the channel region with a gate insulating film interposed therebetween and extending in the second direction intersecting the first direction in plan view, and a surrounding part that extends to surround the semiconductor layer from the main-line part at a position that is separated from the channel region by a predetermined distance in the second direction in plan view.

8. (Withdrawn) The electro-optical device according to Claim 7, the scanning line further including a vertical protrusion that protrudes from the surrounding part in a vertical direction to the substrate.

9. (Previously Presented) The electro-optical device according to Claim 1, the thin film transistor including a semiconductor layer having a channel region that extends in the first direction, and

the scanning line including a main-line part including the gate electrode of the thin film transistor that faces the channel region with the gate insulating film interposed therebetween and extending in the second direction intersecting the first direction in plan view, and a vertical protrusion that protrudes downwardly from the main-line part at a position that is separated from the channel region by a predetermined distance in the second direction in plan view.

10. (Previously Presented) An electro-optical device according to Claim 9, further comprising:

above the substrate, a lower light-shielding film covering at least the channel region from the lower side thereof,

the vertical protrusion contacting the lower light-shielding film at a front end.

11. (Previously Presented) The electro-optical device according to Claim 9, further comprising:

above the substrate, a lower light-shielding film covering at least the channel region from the lower side thereof,

the vertical protrusion not contacting the lower light-shielding film at the front end.

12. (Previously Presented) The electro-optical device according to Claim 1, the thin film transistor including a semiconductor layer having a channel region that extends in the first direction,

the scanning line including the main-line part including the gate electrode of the thin film transistor that faces the channel region with the gate insulating film interposed therebetween and extending in the second direction intersecting the first direction in plan view, and

the main-line part being disposed inside a groove engraved in the substrate and including an inside-groove part that covers at least a part of the channel region from the side thereof.

13. (Previously Presented) The electro-optical device according to Claim 1, the scanning line including a light-shielding film containing metal or alloy.

14. (Currently Amended) The electro-optical device according to Claim 1, one of ~~a pair of the~~ electrodes constituting the storage capacitor constituting a part of a capacitive line formed along the second direction, and

the capacitive line being made of a multi-layered film including a low-resistive film.

15. (Previously Presented) The electro-optical device according to Claim 1, the pixel electrode being electrically connected to an other layer of a laminated structure through a titanium simple substance, a tungsten simple substance, a compound of titanium and tungsten, or a stack thereof.

16. (Previously Presented) The electro-optical device according to Claim 15, the laminated structure further including an interlayer insulating film provided as a base of the pixel electrode,

a contact hole being formed in the interlayer insulating film to electrically connect the pixel electrode thereto, and

a film being formed as at least an inside surface of the contact hole and a lower layer of the pixel electrode, the film including a titanium simple substance, a tungsten simple substance, a compound of titanium or tungsten, or a stack thereof.

17. (Currently Amended) The electro-optical device according to Claim 1, wherein the data line is formed of the same film as one of ~~a pair of the~~ electrodes which constitute the storage capacitor.

18-19. (Canceled).

20. (Currently Amended)) The electro-optical device according to ~~Claim 2,~~  
Claim 1, at least some elements of the scanning line, the data line, ~~a pair of the~~ electrodes  
constituting the storage capacitor, and the ~~shielding light-blocking shield~~ layer being made of  
light-shielding material, and

at least some elements thereof constitute an embedded light-shielding film in  
the laminated structure.

21. (Currently Amended) The electro-optical device according to ~~Claim 1,~~ Claim  
20, further comprising:

the light-shielding film being disposed in the light-shielding regions,

the light-shielding film including a metal layer that contains a high-melting-  
point metal simple substance or metal compound, and a barrier layer that is made of a high-  
melting-point and oxygen-free metal or metal compound laminated on at least one surface of  
the metal layer.

22. (Previously Presented) The electro-optical device according to Claim 21, the  
metal layer of the light-shielding film including a light-shielding metal layer and light-  
absorption metal layer,

the light-absorption metal layer facing the thin film transistor.

23. (Previously Presented) The electro-optical device according to Claim 21, the  
metal layer being interposed between the barrier layers.

24. (Previously Presented) The electro-optical device according to Claim 21, the  
light-shielding film being set at a fixed potential.

25-26. (Canceled)